

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19622	(SiC or (silicon near carbide)) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 20:19
L2	622	1 and polyimide and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 20:20
L3	84	2 and heat\$3 and implant\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 20:20
L4	346	2 not (CVD or (chemical adj vapor adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 20:20
L5	303	4 not (dry near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 21:09
L6	4	("5353498" "5382546" "5383269" "5409865").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/04 21:09
L7	36	("5602059").URPN.	USPAT	OR	OFF	2007/12/04 21:09
S1	11	"6700631"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:10
S2	2	("6700631").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:13
S3	917	(ion\$1 near2 implant\$3) same (SiC or (silicon near carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:15

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S4	331	S3 and (ion\$1 near2 implant\$3) same temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:14
S5	140	S4 and (ion\$1 near2 implant\$3) near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:14
S6	94	S5 and ((ion\$1 near2 implant\$3) near10 (SiC or (silicon near carbide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:17
S7	94	S6 and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 16:18
S8	60	S7 and ((sic or (silicon near carbide)) near4 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 18:40
S9	2	("5628871").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 21:07
S10	5206	photosensitive near2 polyimide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 18:41
S11	3016	S10 and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 18:41
S12	652	S11 and polyimide.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 18:42
S13	443	S12 and resin.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 18:42

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S14	89	(ion\$1 near2 implant\$3) and (polyimide near3 mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 20:06
S15	21	S14 not photoresist not ((dry adj etch\$3) or RIE or (plasma adj etch\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 20:19
S16	1	10/528440	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 20:19
S17	430	polyimide near10 (wet adj etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:04
S18	30	S17 and (SiC or (silicon near carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/17 22:01
S19	8446	"17" and ((wet adj etch\$3) same (HF or hydrofluoric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:02
S20	4	"L17" and ((wet adj etch\$3) same (HF or hydrofluoric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:02
S21	62	polyimide near10 (wet adj etch\$3) and (HF or hydrofluoric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:04
S22	62	(polyimide near10 (wet adj etch\$3)) and (HF or hydrofluoric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:17
S23	2	("6700631").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/18 02:17

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S24	195	438/369.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/04 20:18
S25	24008	implant\$3.clm.	US-PGPUB	OR	OFF	2007/12/04 11:50
S26	508	S25 and (SiC or (silicon near2 carbide)).clm.	US-PGPUB	OR	OFF	2007/12/04 11:50
S27	15	S26 and polyimide.clm.	US-PGPUB	OR	OFF	2007/12/04 11:50
S28	282	S26 and (thickness.clm. or depth.clm.)	US-PGPUB	OR	OFF	2007/12/04 11:52
S29	95	S28 and (depth near6 implant\$3)	US-PGPUB	OR	OFF	2007/12/04 11:52
S30	30	S28 and (depth near6 implant\$3).clm.	US-PGPUB	OR	OFF	2007/12/04 12:19
S31	114062	sic or (silicon near2 carbide)	US-PGPUB; USPAT; JPO	OR	OFF	2007/12/04 12:19
S32	7804	S31 and implant\$3 and ion\$1	US-PGPUB; USPAT; JPO	OR	OFF	2007/12/04 12:19
S33	886	S32 and polyimide	US-PGPUB; USPAT; JPO	OR	OFF	2007/12/04 12:19
S34	97	S33 and ((mask or photoresist or resist) near10 polyimide)	US-PGPUB; USPAT; JPO	OR	OFF	2007/12/04 12:20